



74AUP2G125

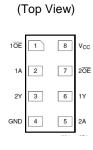
DUAL 3-STATE BUFFER

Description

The Advanced Ultra Low Power (AUP) CMOS logic family is designed for low power and extended battery life in portable applications.

The 74AUP2G125 is a dual 3-State Buffer. Each buffer has an individual output enable pin while asserted HIGH will place the output in a high impedance state. The device is designed for operation over a power supply range of 0.8 V to 3.6 V. The device is fully specified for partial power down applications using I_{OFF} . The I_{OFF} circuitry disables the output preventing damaging current backflow when the device is powered down.

Pin Assignments



X2-DFN1210-8

Features

- Advanced Ultra Low Power (AUP) CMOS
- Supply Voltage Range from 0.8 V to 3.6 V
- ± 4 mA Output Drive at 3.0 V
- Low Static Power Consumption
- Icc < 0.9 uA
- Low Dynamic Power Consumption
- C_{PD} = 6 pF Typical at 3.6 V
- Schmitt trigger action at all inputs make the circuit tolerant for slower input rise and fall time. The hysteresis is typically 250 mV at Vcc = 3.0V
- IOFF Supports Partial-Power-Down Mode Operation
- ESD Protection per JESD 22
 - Exceeds 200-V Machine Model (A115) Exceeds 2000-V Human Body Model (A114) Exceeds 1000-V Charged Device Model (C101)
- Latch-Up Exceeds 100mA per JESD 78, Class I
- Leadless Packages per JESD30E
- DFN1210 Denoted as X2-DFN1210-8
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

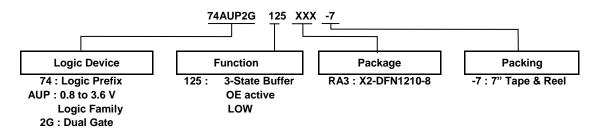
Applications

- Suited for Battery and Low Power Needs
- Wide array of products such as:
 - Tablets, E-readers
 - Cell Phones, Personal Navigation / GPS
 - MP3 Players, Cameras, Video Recorders
 - PCs, Ultrabooks, Notebooks, Netbooks
 - Computer Peripherals, Hard Drives, SSD, CD/DVD ROM
 - TV, DVD, DVR, Set-Top Box

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.





Device	Package	Package	Package	7" Tape and Reel			
Device	Code	(Notes 4 & 5)	Size	Quantity	Part Number Suffix		
74AUP2G125RA3-7	RA3	X2-DFN1210-8	1.2mm X 1.0 mm X 0.35mm 0.3 mm lead pitch	5,000/Tape & Reel	-7		

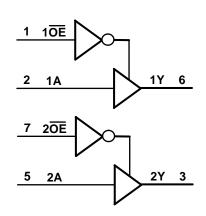
Notes: 4. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

5. The taping orientation is located on our website at http://www.diodes.com/datasheets/ap02007.pdf

Pin Descriptions

Pin Name	Pin NO.	Description
1 OE	1	Output Enable active LOW
1A	2	Data Input
2Y	3	Data Output
GND	4	Ground
2A	5	Data Input
1Y	6	Data Output
2 OE	7	Output Enable active LOW
V _{cc}	8	Supply Voltage

Logic Diagram



Function Table

Inp	Output				
OE	OE A				
L	н	Н			
L	L	L			
Н	Х	Z			



Absolute Maximum Ratings (Notes 6 & 7)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	kV
ESD CDM	Charged Device Model ESD Protection	1	kV
Vcc	Supply Voltage Range	-0.5 to +4.6	V
VI	Input Voltage Range	-0.5 to +4.6	V
Vo	Voltage Applied to Output in High or Low State	-0.5 to V _{CC} +0.5	V
lıк	Input Clamp Current VI < 0	50	mA
loк	Output Clamp Current (V _O < 0)	50	mA
lo	Continuous Output Current ($V_O = 0$ to V_{CC})	±20	mA
Icc	Continuous Current Through V _{CC}	50	mA
IGND	Continuous Current Through GND	-50	mA
TJ	Operating Junction Temperature	-40 to +150	°C
T _{STG}	Storage Temperature	-65 to +150	°C

Notes:

es: 6. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.

7. Forcing the maximum allowed voltage could cause a condition exceeding the maximum current or conversely forcing the maximum current could cause a condition exceeding the maximum voltage. The ratings of both current and voltage must be maintained within the controlled range.

Recommended Operating Conditions (Note 8)

Symbol	Param	eter	Min	Max	Unit
V _{CC}	Operating Voltage		0.8	3.6	V
VI	Input Voltage		0	3.6	V
Vo	Output Voltage		0	Vcc	V
		$V_{CC} = 0.8V$	—	-20	μA
		$V_{CC} = 1.1V$	—	-1.1	
	I _{OH} High-Level Output Current	$V_{CC} = 1.4V$	—	-1.7	
ЮН		V _{CC} = 1.65V	—	-1.9	mA
		$V_{CC} = 2.3V$	—	-3.1	
		$V_{CC} = 3.0V$	—	-4	
		$V_{CC} = 0.8V$	—	20	μA
		V _{CC} = 1.1V	—	1.1	
		$V_{CC} = 1.4V$	—	1.7	
I _{OL}	Low-Level Output Current	V _{CC} = 1.65V	—	1.9	mA
		$V_{CC} = 2.3V$	—	3.1	
		$V_{CC} = 3.0V$	—	4	
Δt/ΔV	Input Transition Rise or Fall Rate	V _{CC} = 0.8V to 3.6V	—	200	ns/V
T _A	Operating Free-Air Temperature		-40	125	°C

Note: 8. Unused inputs should be held at V_{CC} or Ground.



Electrical Characteristics

Sumbol	Doromotor	Toot Conditions	v	T _A = +	-25°C	T _A = -40°C	to +85°C	11-14	
Symbol	Parameter	Test Conditions	Vcc	Min	Max	Min	Max	Unit	
		—	0.8V to 1.65V	0.80 X V _{CC}	_	0.80 X V _{CC}	—		
V	High-Level Input	_	1.65V to 1.95V	0.65 X V _{CC}	_	0.65 X V _{CC}	_	v	
VIH	Voltage	_	2.3V to 2.7V	1.6	—	1.6	—	v	
		—	3.0V to 3.6V	2.0	—	2.0	—		
		—	0.8V to 1.65V	_	0.30 X V _{CC}		0.30 X V _{CC}		
VIL	Low-Level Input	—	1.65V to 1.95V	—	0.35 X V_{CC}	_	$0.35 \text{ X V}_{\text{CC}}$	v	
VIL	Voltage	—	2.3V to 2.7V	—	0.7		0.7	Ň	
		—	3.0V to 3.6V	—	0.9		0.9		
		I _{OH} = -20µА	0.8V to 3.6V	V _{CC} – 0.1	—	V _{CC} – 0.1	—		
		I _{OH} = -1.1mA	1.1V	0.75 X V _{CC}	—	0.7 X V _{CC}	—		
	, он Voltage	I _{OH} = -1.7mA	1.4V	1.11	—	1.03	—		
		I _{OH} = -1.9mA	1.65V	1.32	—	1.3	—	v	
VOH		I _{OH} = -2.3mA	0.01/	2.05	—	1.97	—	v	
		I _{OH} = -3.1mA	2.3V	1.9	_	1.85	—		
		I _{OH} = -2.7mA	0) (2.72	—	2.67	—		
		I _{OH} = -4mA	3V	2.6	—	2.55	—		
		I _{OL} = 20μΑ	0.8V to 3.6V	—	0.1	_	0.1		
		$I_{OL} = 1.1 \text{mA}$	1.1V	—	0.3 X V _{CC}		0.3 X V _{CC}		
		I _{OL} = 1.7mA	1.4V	_	0.31		0.37]	
	Low-Level Output	I _{OL} = 1.9mA	1.65V		0.31		0.35		
Vol	Voltage	$I_{OL} = 2.3 \text{mA}$		_	0.31		0.33	V	
		$I_{OL} = 3.1 \text{mA}$	2.3V		0.44		0.45	-	
		$I_{OL} = 2.7 \text{mA}$			0.31		0.33		
		$I_{OL} = 4mA$	3V		0.44		0.45	1	
lı	Input Current	A or B Input	0 to 3.6V	_	± 0.1	_	± 0.5	μA	
I _{OZ}	Z-State Leakage Current	$V_1 = GND \text{ to } 3.6V$ $V_1 \text{ or } V_0 = 0V \text{ to } 3.6V$	0 to 3.6V	_	0.2	_	± 0.5	μA	
I _{OFF}	Power Down	V_1 or $V_0 =$	0 V		± 0.2		± 0.5	μA	
	Leakage Current	0V to 3.6V	0 0					· · ·	
ΔI_{OFF}	Delta Power Down Leakage Current	$V_1 \text{ or } V_0 =$ 0V to 3.6V	0 V to 0.2V	_	0.2	_	0.6	μA	
I _{CC}	Supply Current	$V_I = GND \text{ or } V_{CC}, I_O = 0$	0.8 V to 3.6V	—	0.5	—	0.9	μA	
		Data Input at V _{CC} –0.6 V OE= GND I _O =0 A	3.3V	_	40	_	50	μA	
ΔI _{cc}	ΔI _{cc} Additional Supply C Current	OE Input at VCC –0.6 V Data Input= GND or Vcc I ₀ =0 A	3.3V	_	110	_	120	μA	
		OE Input at VCC Data Input= GND to $3.6 \vee I_0=0 A$	0.8V to 3.6V	_	1	_	1	μA	



Electrical Characteristics (cont.)

Symbol	Parameter	Test Conditions	V	T _A = -40°C te	o +125°C	Unit	
Symbol	Farameter	rest conditions	Vcc	Min	Max	Unit	
		—	0.8V to 1.65V	0.80 X V _{CC}	—		
VIH	High-Level Input	—	1.65V to 1.95V	0.70 X V _{CC}	_	v	
VIH	Voltage	—	2.3V to 2.7V	1.6	—	v	
		—	3.0V to 3.6V	2.0	—		
		—	0.8V to 1.65V	—	0.25 X V _{CC}		
VIL	Low-Level Input	—	1.65V to 1.95V	_	0.30 X V _{CC}	v	
۷IL	Voltage	—	2.3V to 2.7V	—	0.7	v	
		—	3.0V to 3.6V	—	0.9		
		I _{OH} = -20μA	0.8V to 3.6V	V _{CC} – 0.11			
		I _{OH} = -1.1mA	1.1V	0.6 X V _{CC}	—		
		I _{OH} = -1.7mA	1.4V	0.93	—		
Maria	High-Level Output	I _{OH} = -1.9mA	1.65V	1.17	—	v	
V _{OH}	Voltage	I _{OH} = -2.3mA	2.21/	1.77	—	v	
		I _{OH} = -3.1mA	2.3V	1.67	—		
		I _{OH} = -2.7mA	3V	2.40	—		
		$I_{OH} = -4mA$		2.30	_		
		I _{OL} = 20μΑ	0.8V to 3.6V	—	0.11		
		I _{OL} = 1.1mA	1.1V	—	0.33 X V _{CC}		
		I _{OL} = 1.7mA	1.4V	_	0.41		
	Low-Level Output	I _{OL} = 1.9mA	1.65V	_	0.39		
Vol	Voltage	I _{OL} = 2.3mA	2.01/	_	0.36	V	
		I _{OL} = 3.1mA	2.3V	_	0.50		
		I _{OL} = 2.7mA	a) (_	0.36		
		$I_{OL} = 4mA$	3V	_	0.50		
II.	Input Current	A or B Input, $V_I = GND$ to 3.6V	0 to 3.6V	_	± 0.75	μA	
I _{OZ}	Z-State Leakage Current	V_1 or $V_0 = 0V$ to 3.6V	0 to 3.6V	—	± 1.5	μA	
I _{OFF}	Power Down Leakage Current	V_1 or $V_0 = 0V$ to 3.6V	0	_	± 3.5	μA	
ΔI_{OFF}	Delta Power Down Leakage Current	V_1 or $V_0 = 0V$ to 3.6V	0V to 0.2V	_	± 2.5	μA	
Icc	Supply Current	$V_I = GND \text{ or } V_{CC}, I_O = 0$	0.8V to 3.6V	—	3.0	μA	
		Data Input at V _{cc} –0.6 V OE= GND I _o =0 A	3.3V	_	75	μA	
ΔI _{cc}	ΔI _{cc} Additional Supply C Current I C V	OE Input at VCC –0.6 V Data Input= GND or Vcc I ₀ =0 A	3.3V	_	180	μA	
		OE Input at VCC Data Input= GND to 3.6 V I ₀ =0 A	0.8V to 3.6V	_	1	μA	



Operating and Package Characteristics (@T_A = +25°C, unless otherwise specified.)

	Parameter	Test Condition	s	V _{CC}	Тур	Unit	
				0.8V	6.5		
				1.2V ± 0.1V	6.3		
0	Power Dissipation	f = 1MHz		1.5V ± 0.1V	6.3	~	
Cpd	C _{pd} Capacitance per gate	Output Enabled No Load		1.8V ± 0.15V	6.2	pF	
		No Loud		2.5V ± 0.2V	6.2		
				3.3V ± 0.3V	6.1		
Ci	Input Capacitance	$V_i = V_{CC} \text{ or } G$	SND	0V or 3.3V	1.5	pF	
•	Outrut Consolitores	Output Enabled	VO=Gnd	0 V	2.9	pF	
Co	Output Capacitance	Output Disabled VO=	=Gnd or Vcc	0V or 3.6V	2.1	pF	
θ_{JA}	Thermal Resistance Junction-to-Ambient	X2-DFN1210-8 (Note 9)		—	395	°C/W	
θ_{JC}	Thermal Resistance Junction-to-Case	X2-DFN1210-8	(Note 9)	—	236	°C/W	

Note: 9. Test condition, X2-DFN1210-8 device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.



Switching Characteristics

	_	_		T _A = +25°C			T _A = -40°C	C to +85°C	T _A = -40°C		
Parameter	From Input	To Output	V _{CC}	Min	Тур	Max	Min	Max	Min	Max	Unit
			0.8V	_	20.6	—	_	—	_	_	
			1.2V ± 0.1V	2.8	5.5	12.6	2.5	14.0	2.5	17	1
	۸	A Y	1.5V ± 0.1V	2.2	3.9	7.3	2.0	7.5	2.0	8.1	
tpd	t _{pd} A Y	1.8V ± 0.15V	1.9	3.2	4.8	1.7	6.1	1.7	6.7	ns	
			2.5V ± 0.2V	1.6	2.6	3.6	1.4	4.3	1.4	4.9	
		3.3V ± 0.3V	1.4	2.4	3.1	1.2	3.9	1.2	4.4		
		Y	0.8V	_	69.9	_	_	—	_	_	- ns
			1.2V ± 0.1V	3.1	6.1	14.2	2.9	20	2.9	22.2	
4			1.5V ± 0.1V	2.5	4.2	7.9	2.3	9.2	2.3	10.0	
t _{en}	ŌE	Ť	1.8V ± 0.15V	2.1	3.4	6.1	2.0	7.4	2.0	8.2	
			2.5V ± 0.2V	1.8	2.6	4.4	1.7	5.4	1.7	6.0	
			3.3V ± 0.3V	1.7	2.4	4.0	1.7	4.6	1.7	5.1	
			0.8V	_	14.3	_	_	—	_	_	
			1.2V ± 0.1V	2.7	4.3	9.4	2.7	10.6	2.7	11.8	1
t _{dis} \overline{OE}	v	1.5V ± 0.1V	2.1	3.2	6.4	2.1	7.3	2.1	8.2		
	Y -	1.8V ± 0.15V	2.0	3.0	5.5	2.0	6.3	2.0	7.1	ns	
			2.5V ± 0.2V	1.4	2.2	3.7	1.4	4.2	1.4	5.1	
			3.3V ± 0.3V	1.7	2.5	4.4	1.7	4.6	1.7	5.4]

$C_L = 10 pF$, See Figure 1

Deremeter	From	То	М		T _A = +25°C	;	T _A = -40°C	C to +85°C	T _A = -40°C	to +125°C	Unit
Parameter	Input	Output	V _{CC}	Min	Тур	Max	Min	Max	Min	Max	Unit
			0.8V	_	24.0	_	_	_	_	_	
t _{od} A		1.2V ± 0.1V	3.2	6.4	14.8	3.0	16.6	3.0	18.2		
	Y	1.5V ± 0.1V	2.1	4.5	8.8	1.9	9.1	1.9	9.4	ns	
t _{pd}	A	T	1.8V ± 0.15V	1.9	3.8	5.5	1.7	6.8	1.7	7.6	115
			2.5V ± 0.2V	2.1	3.2	4.2	1.6	5.3	1.6	5.9	
			3.3V ± 0.3V	1.8	3.0	3.8	1.6	4.6	1.6	5.2	
		Y	0.8V	_	73.7	_	_	_	_	_	- - ns
			1.2V ± 0.1V	3.6	6.9	16.2	3.4	22.8	3.4	25.2	
	OE		1.5V ± 0.1V	2.3	4.8	9.2	2.2	10.3	2.2	11.3	
t _{en}	ÛE		1.8V ± 0.15V	2.0	3.9	7.0	1.9	8.2	1.9	8.9	
			2.5V ± 0.2V	1.8	3.2	5.2	1.7	6.4	1.7	7.1	
			$3.3V \pm 0.3V$	1.7	3.0	5.1	1.7	5.6	1.7	6.2	
			0.8V	_	32.7	—	—	—	—	—	
			1.2V ± 0.1V	3.4	5.4	11.4	3.4	12.7	3.4	14.3	
		V	1.5V ± 0.1V	2.2	4.1	7.9	2.2	8.9	2.2	10.2	
t _{dis}	ŌĒ	Y 1	1.8V ± 0.15V	2.2	4.2	7.0	1.9	8.0	1.9	8.9	ns
			2.5V ± 0.2V	1.7	3.0	4.8	1.7	5.7	1.7	6.4	
			3.3V ± 0.3V	2.1	3.8	6.5	1.7	6.8	1.7	7.7	



Switching Characteristics (cont.)

$C_L = 15 pF$, See Figure 1

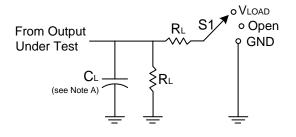
Parameter	From	То	Vcc		T _A = +25°C	;	T _A = -40°C	C to +85°C	T _A = -40°C	to +125°C	Unit
Farameter	Input	Output	VCC	Min	Тур	Max	Min	Max	Min	Max	Unit
			0.8V	_	27.4	_	_	_	_	_	
			1.2V ± 0.1V	3.6	7.2	15.8	3.3	22.4	3.3	22.5	
t _{pd} A	Y	1.5V ± 0.1V	3.0	5.1	8.8	2.5	9.8	2.5	10.9	ns	
	ř	1.8V ± 0.15V	2.2	4.3	6.3	2.0	7.9	2.0	8.8		
			2.5V ± 0.2V	2.0	3.7	4.9	1.8	6.0	1.8	6.7	
			3.3V ± 0.3V	2.0	3.5	4.4	1.8	5.4	1.8	6.1	_
		Y	0.8V	_	77.5	_	_	_	_	_	
			1.2V ± 0.1V	4.0	7.7	18.2	3.7	21.8	3.7	23.5	- ns
			1.5V ± 0.1V	3.0	5.3	10.1	2.5	11.8	2.5	12.8	
t _{en}	ŌĒ		1.8V ± 0.15V	2.3	4.4	7.8	2.1	9.2	2.1	10.2	
			2.5V ± 0.2V	2.1	3.6	6.0	2.0	7.3	2.0	8.2	
			3.3V ± 0.3V	2.0	3.5	5.7	1.9	6.4	1.9	7.2	1
			0.8V		60.8	_	—	_		_	
			1.2V ± 0.1V	4.3	6.5	13.9	3.7	15.5	3.7	15.7	1
		V	1.5V ± 0.1V	3.0	5.0	8.8	2.5	9.7	2.5	9.8	
t _{dis}	ŌĒ	Y	1.8V ± 0.15V	3.0	5.3	8.8	2.1	10.3	2.1	10.5	ns
			2.5V ± 0.2V	2.1	3.8	8.2	2.0	8.4	2.0	8.6	
			3.3V ± 0.3V	2.9	5.0	8.6	1.9	9.2	1.9	9.4	1

C_L = 30pF, See Figure 1

Parameter	From	То	V		T _A = +25°C	;	T _A = -40°C	C to +85°C	T _A = -40°C	to +125°C	Unit
Farameter	Input	Output	V _{cc}	Min	Тур	Max	Min	Max	Min	Max	Unit
			0.8V	—	37.4	_	—	—		—	
		1.2V ± 0.1V	4.8	9.5	21	4.4	24.9	4.4	25		
	А	Y	1.5V ± 0.1V	4.0	6.7	10.8	3.0	13.0	3.0	14.5	200
t _{pd}	A	T	1.8V ± 0.15V	2.9	5.6	8.4	2.6	10.3	2.6	11.5	ns
			2.5V ± 0.2V	2.7	4.8	6.3	2.5	7.8	2.5	8.7	
			3.3V ± 0.3V	2.7	4.6	6	2.5	7.5	2.5	8.3	_
		Y	0.8V	_	88.9	_	_	_	_	_	- ns
			1.2V ± 0.1V	5.2	9.9	23.8	4.8	27.4	4.8	30.4	
	OE		1.5V ± 0.1V	4.0	6.8	13.0	3.1	15.1	3.1	16.9	
t _{en}	ÛE		1.8V ± 0.15V	3.0	5.6	10.2	2.8	12.2	2.8	13.6	
			2.5V ± 0.2V	2.7	4.8	7.8	2.6	9.4	2.6	10.6	
			$3.3V \pm 0.3V$	2.7	4.6	7.8	2.6	9.0	2.6	10.0	
			0.8V	—	49.9	—	—	_		—	
			1.2V ± 0.1V	6.0	9.9	16.0	4.8	17.8	4.8	19.8	
		v	1.5V ± 0.1V	4.4	7.7	11.5	3.1	13.0	3.1	14.5	20
Ldis	t _{dis} OE	OE Y -	1.8V ± 0.15V	5.1	8.7	13.3	2.8	14.9	2.8	16.6	ns
			2.5V ± 0.2V	3.6	6.2	9.1	2.6	10.3	2.6	11.5	
			$3.3V \pm 0.3V$	5.2	8.7	13.7	2.6	14.0	2.6	17.0	



Parameter Measurement Information

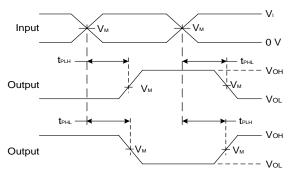


TEST	S1	R∟
t _{PLH} /t _{PHL}	Open	1MΩ
t _{PLZ} /t _{PZL}	Vload	5ΚΩ
t _{PHZ} /t _{PZH}	GND	5ΚΩ

Vcc	In	outs	V	v		V۸
VCC	VI	t _r /t _f	V _M	V _{LOAD}	CL	VΔ
0.8V	Vcc	≤3ns	V _{CC} /2	2 X V _{CC}	5, 10, 15, 30pF	0.1 V
1.2V±0.1V	Vcc	≤3ns	V _{CC} /2	$2 X V_{CC}$	5, 10, 15, 30pF	0.1 V
1.5V±0.1V	V _{CC}	≤3ns	V _{CC} /2	2 X V _{CC}	5, 10, 15, 30pF	0.1 V
1.8V ±0.15V	V _{CC}	≤3ns	V _{CC} /2	2 X V _{CC}	5, 10, 15, 30pF	0.15 V
2.5V±0.2V	Vcc	≤3ns	V _{CC} /2	2 X V _{CC}	5, 10, 15, 30pF	0.15 V
3.3V±0.3V	Vcc	≤3ns	V _{CC} /2	2 X V _{CC}	5, 10, 15, 30pF	0.3V



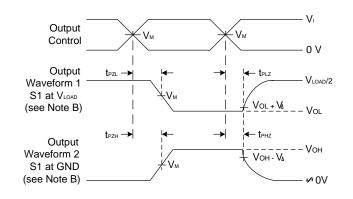
Voltage Waveform Pulse Duration



Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs

Figure 1 Load Circuit and Voltage Waveforms

- Notes: A. Includes test lead and test apparatus capacitance.
 - B. All pulses are supplied at pulse repetition rate \leq 10 MHz.
 - C. Inputs are measured separately one transition per measurement.
 - D. t_{PLZ} and t_{PHZ} are the same as $t_{\text{dis.}}$
 - E. t_{PZL} and t_{PZH} are the same as t_{EN}
 - F. t_{PLH} and t_{PHL} are the same as $t_{PD.}$



Voltage Waveform Enable and Disable Times Low and High Level Enabling



Marking Information

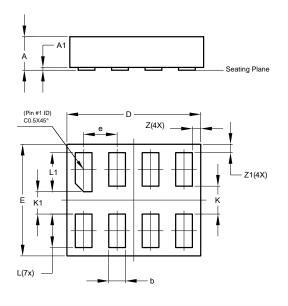
X2-DFN1210-8

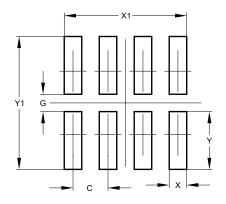


Part Number	Package	Identification Code
74AUP2G125RA3-7	X2-DFN1210-8	JT

X2-DFN1210-8 Package Outline Dimensions and Suggested Pad Layout

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.





	X2-DFN1210-8				
Dim	Min	Max	Тур		
Α	-	0.35	0.30		
A1	0	0.03	0.02		
b	0.10	0.20	0.15		
D	1.15	1.25	1.20		
Е	0.95	1.05	1.00		
е	-	-	0.30		
К	-	-	0.25		
K 1	-	-	0.20		
L	0.25	0.35	0.30		
L1	0.30	0.40	0.35		
Z	0.050	0.100	0.075		
Z1	0.050	0.100	0.075		
All Dimensions in mm					

Dimensions	Value (in mm)	
С	0.300	
G	0.150	
х	0.150	
X1	1.050	
Y	0.500	
Y1	1.150	



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